

FIG. 1a  
(PRIOR ART)

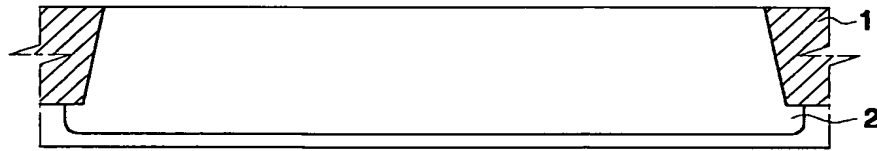


FIG. 1b  
(PRIOR ART)

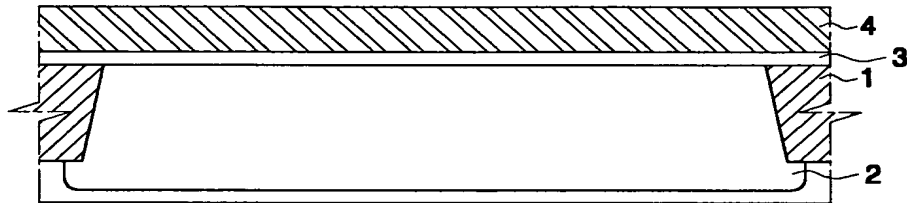


FIG. 1c  
(PRIOR ART)

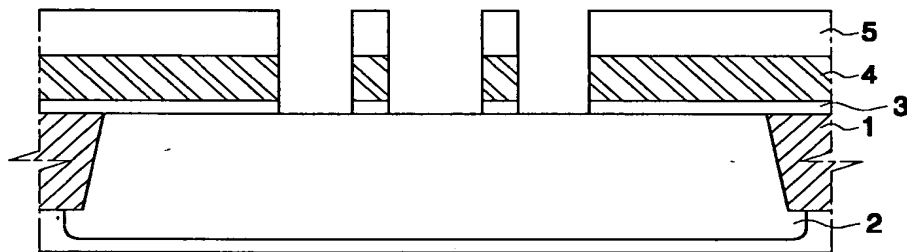


FIG. 1d  
(PRIOR ART)

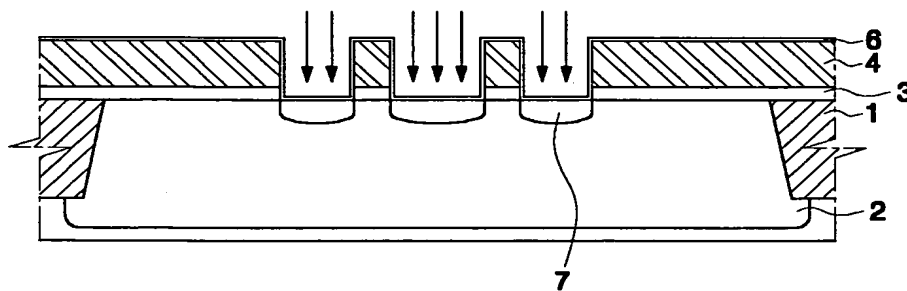


FIG. 1e  
(PRIOR ART)

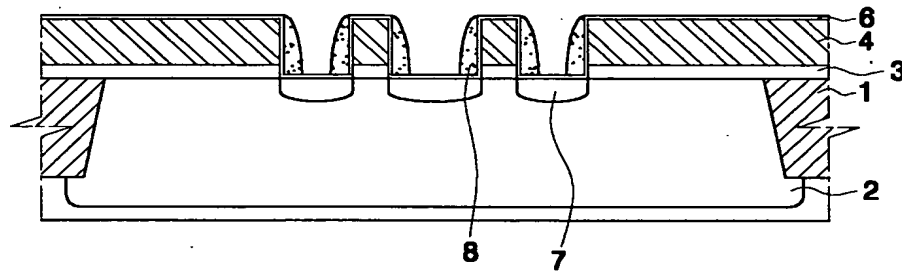


FIG. 1f  
(PRIOR ART)

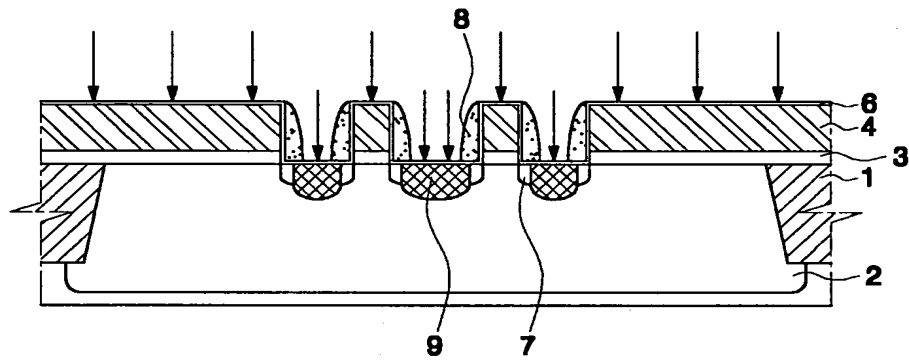


FIG. 1g  
(PRIOR ART)

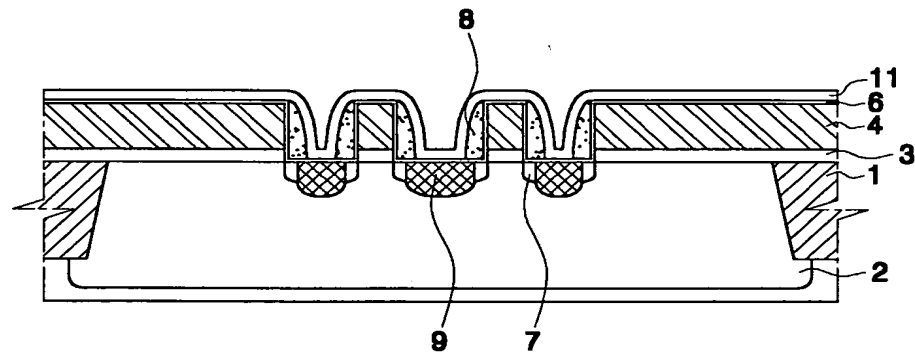


FIG. 1h  
 (PRIOR ART)

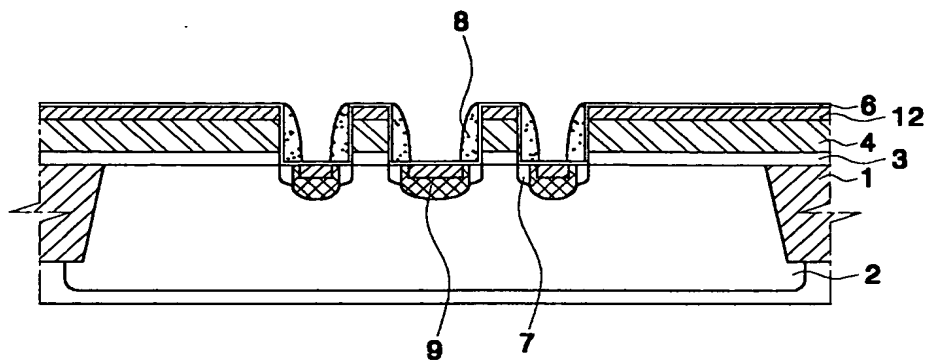


FIG. 1i  
 (PRIOR ART)

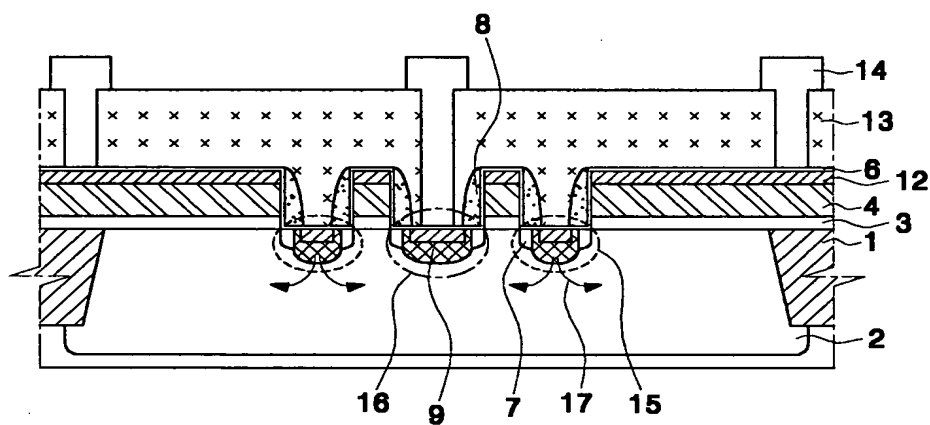


FIG. 2a

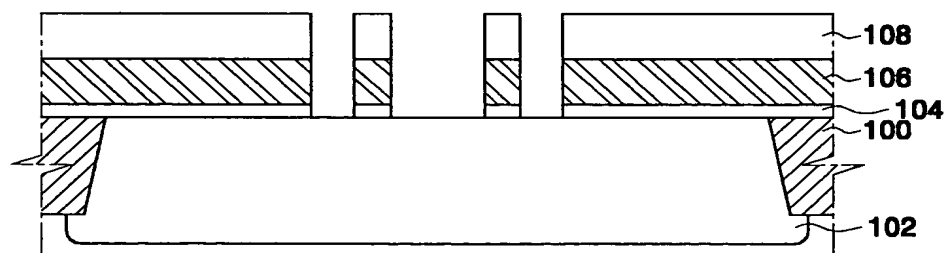


FIG. 2b

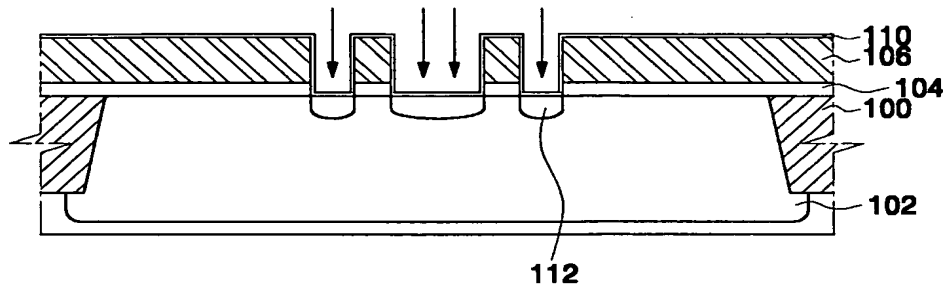


FIG. 2c

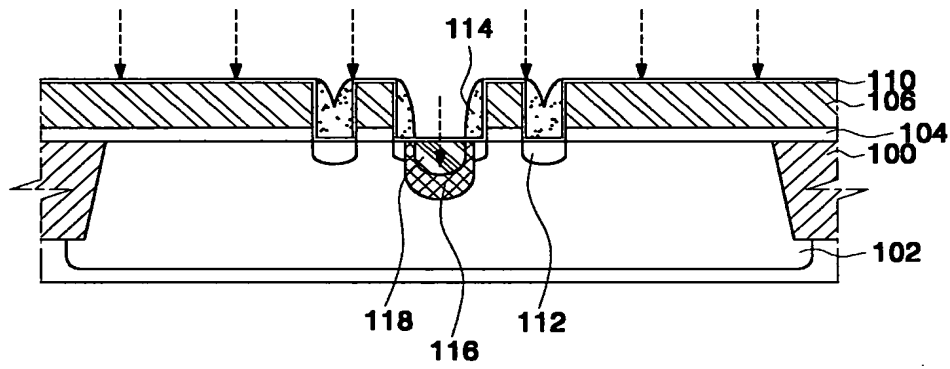


FIG. 2d

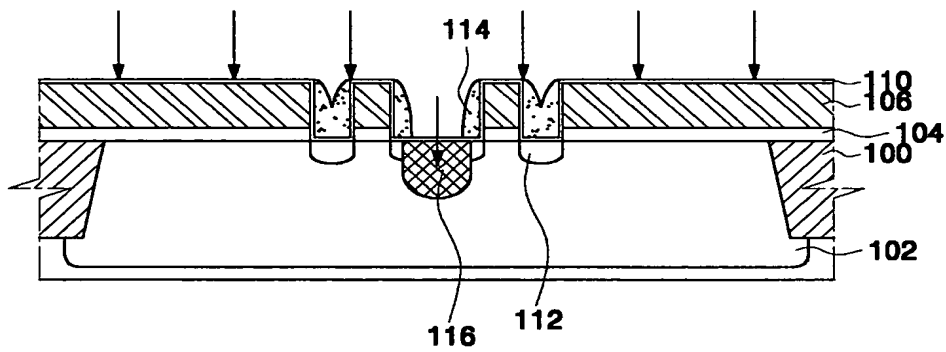


FIG. 2e

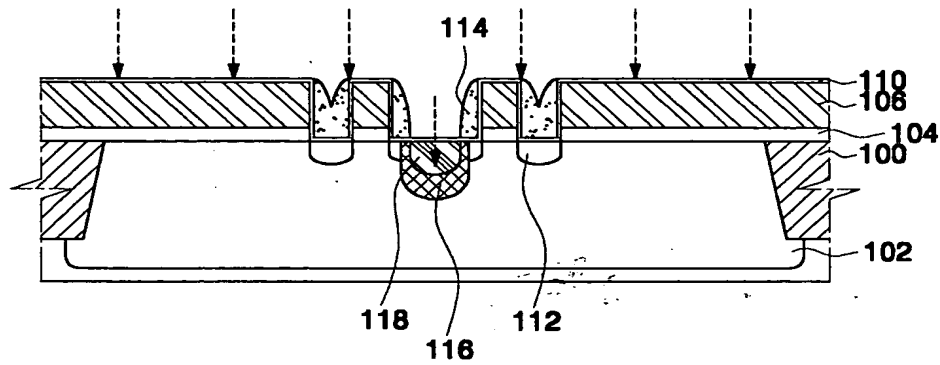


FIG. 2f

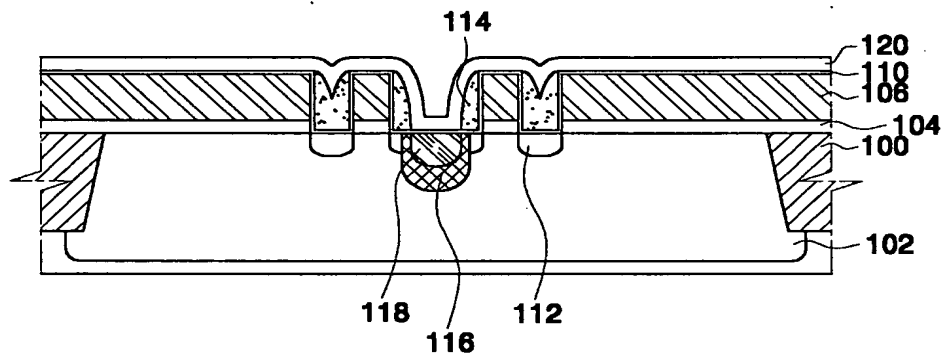
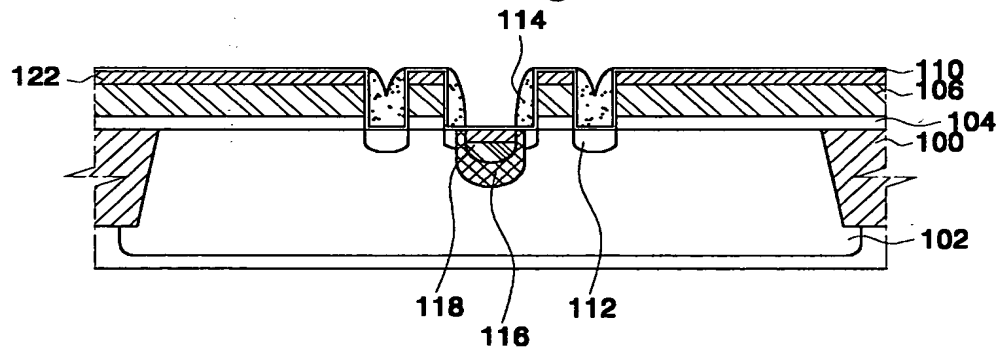


FIG. 2g



This cross-sectional view shows a semiconductor device with a central gate structure 114. The gate structure is composed of a gate dielectric 110, a gate electrode 106, and a gate spacer 104. The gate electrode 106 is patterned to form a central gate 116 and two side gates 118 and 128. The side gates 118 and 128 are connected to a common source/drain contact 102. The device is formed on a substrate 100, which is covered by a passivation layer 102. The side gates 118 and 128 are connected to a common source/drain contact 102. The device is formed on a substrate 100, which is covered by a passivation layer 102.

FIG. 1 is a cross-sectional view of a semiconductor device 100. The device includes a substrate 102, a base layer 104, and a patterned layer 106. The patterned layer 106 has openings 108. The substrate 102 is shown with a cross-hatched pattern, and the base layer 104 is shown with a diagonal line pattern. The patterned layer 106 is shown with a solid black fill. The openings 108 are shown as rectangular voids in the patterned layer 106.

A cross-sectional view of a substrate assembly. A substrate 100 has a recessed region 102. A conductive layer 104 is formed on the top surface of the substrate 100. The conductive layer 104 includes a central portion 108 and side portions 110. The central portion 108 is recessed into the recessed region 102. Arrows indicate the direction of the conductive layer 104. A wavy line 113 is shown below the recessed region 102.

FIG. 3c

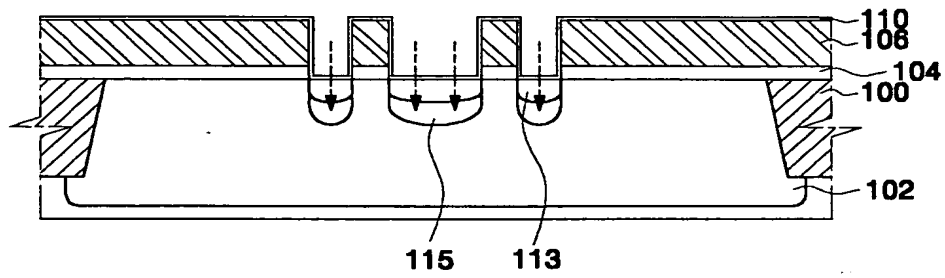


FIG. 3d

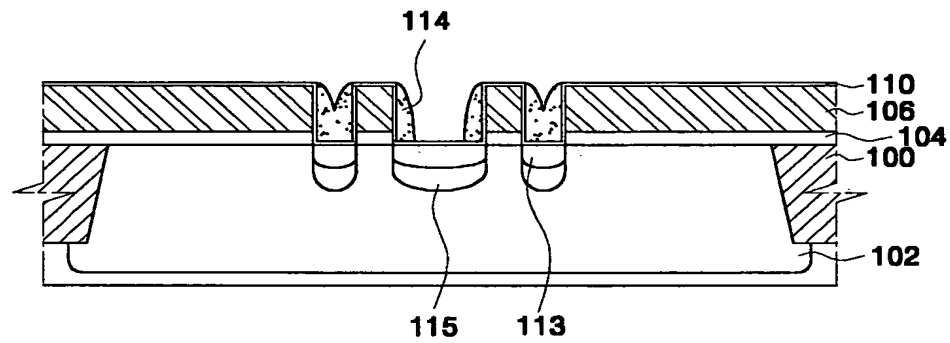


FIG. 3e

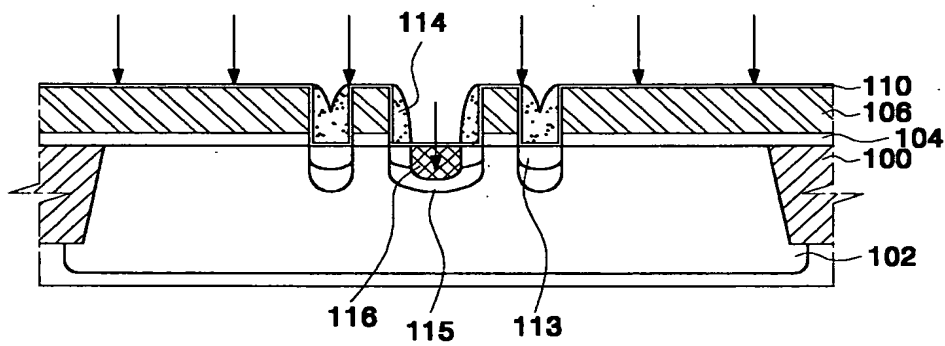


FIG. 3f

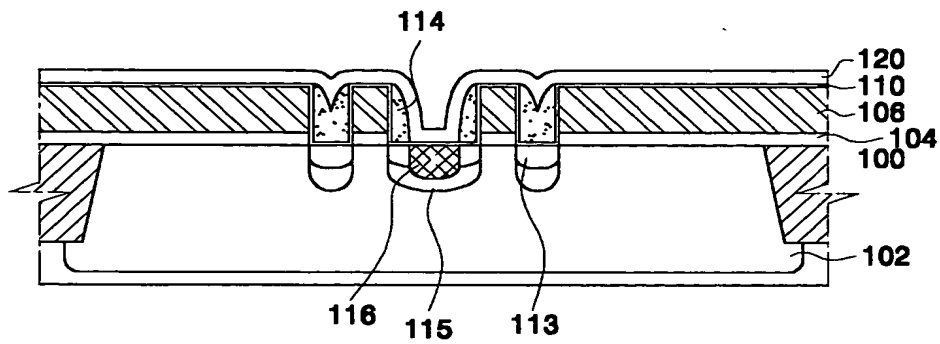


FIG. 3g

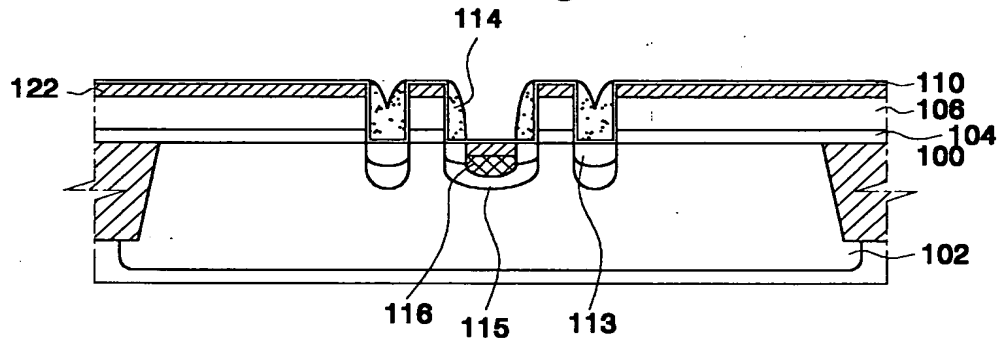


FIG. 3h

